

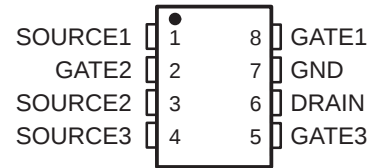
TPIC3302

3-CHANNEL COMMON-DRAIN POWER DMOS ARRAY

SLIS021B – APRIL 1994 – REVISED JULY 1995

- Low $r_{DS(on)}$. . . 0.4 Ω Typ
- High-Voltage Outputs . . . 60 V
- Pulsed Current . . . 5 A Per Channel
- Fast Commutation Speed

D PACKAGE
(TOP VIEW)

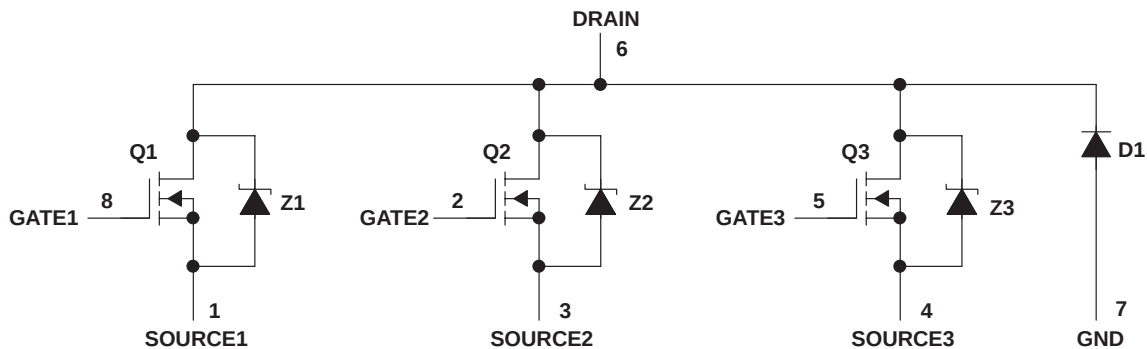


description

The TPIC3302 is a monolithic power DMOS array that consists of three electrically isolated N-channel enhancement-mode DMOS transistors configured with a common drain and open sources. The TPIC3302 is offered in a standard eight-pin small-outline surface-mount (D) package.

The TPIC3302 is characterized for operation over the case temperature range of -40°C to 125°C .

schematic



absolute maximum ratings over operating case temperature range (unless otherwise noted)[†]

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage	100 V
Drain-to-GND voltage	100 V
Gate-to-source voltage, V_{GS}	± 20 V
Continuous drain current, each output, all outputs on, $T_C = 25^{\circ}\text{C}$	1 A
Continuous source-to-drain diode current	1 A
Pulsed drain current, each output, $T_C = 25^{\circ}\text{C}$ (see Note 1 and Figure 6)	5 A
Single-pulse avalanche energy, $T_C = 25^{\circ}\text{C}$, E_{AS} (see Figure 4)	9 mJ
Continuous total power dissipation at (or below) $T_C = 25^{\circ}\text{C}$	0.95 W
Operating virtual junction temperature range, T_J	-40°C to 150°C
Operating case temperature range, T_C	-40°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms, duty cycle = 2%

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electrical characteristics, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$ Drain-to-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	60			V
$V_{GS(th)}$ Gate-to-source threshold voltage	$I_D = 1\ \text{mA}$, $V_{DS} = V_{GS}$	1.5	1.85	2.2	V
$V_{(BR)}$ Reverse drain-to-GND breakdown voltage (across D1)	Drain-to-GND current = $250\ \mu\text{A}$	100			V
$V_{DS(on)}$ Drain-to-source on-state voltage	$I_D = 1\ \text{A}$, $V_{GS} = 10\ \text{V}$, See Notes 2 and 3		0.4	0.475	V
V_F Forward on-state voltage, GND-to-drain	$I_D = 1\ \text{A}$, See Notes 2 and 3		2		V
$V_{F(SD)}$ Forward on-state voltage, source-to-drain	$I_S = 1\ \text{A}$, $V_{GS} = 0$, See Notes 2 and 3		0.9	1.1	V
I_{DSS} Zero-gate-voltage drain current	$V_{DS} = 48\ \text{V}$, $V_{GS} = 0$	$T_C = 25^\circ\text{C}$	0.05	1	μA
		$T_C = 125^\circ\text{C}$	0.5	10	
I_{GSSF} Forward gate current, drain short circuited to source	$V_{GS} = 16\ \text{V}$, $V_{DS} = 0$		10	100	nA
I_{GSSR} Reverse gate current, drain short circuited to source	$V_{SG} = 16\ \text{V}$, $V_{DS} = 0$		10	100	nA
I_{lkg} Leakage current, drain-to-GND	$V_R = 48\ \text{V}$	$T_C = 25^\circ\text{C}$	0.05	1	μA
		$T_C = 125^\circ\text{C}$	0.5	10	
$r_{DS(on)}$ Static drain-to-source on-state resistance	$V_{GS} = 10\ \text{V}$, $I_D = 1\ \text{A}$, See Notes 2 and 3 and Figures 6 and 7	$T_C = 25^\circ\text{C}$	0.4	0.475	Ω
		$T_C = 125^\circ\text{C}$	0.63	0.7	
g_{fs} Forward transconductance	$V_{DS} = 10\ \text{V}$, $I_D = 0.5\ \text{A}$, See Notes 2 and 3	0.85	1.02		S
C_{iss} Short-circuit input capacitance, common source	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$		115	145	pF
C_{oss} Short-circuit output capacitance, common source			60	75	
C_{rss} Short-circuit reverse-transfer capacitance, common source			30	40	

NOTES: 2. Technique should limit $T_J - T_C$ to 10°C maximum, pulse duration $\leq 5\ \text{ms}$.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain diode characteristics, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{rr(SD)}$ Reverse-recovery time	$I_S = 0.5\ \text{A}$, $V_{GS} = 0$, $V_{DS} = 48\ \text{V}$, $di/dt = 100\ \text{A}/\mu\text{s}$, See Figure 1		35		ns
Q_{RR} Total diode charge			0.03		μC

GND-to-drain diode characteristics, $T_C = 25^\circ\text{C}$ (see schematic, D1)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{rr} Reverse-recovery time	$I_F = 0.5\ \text{A}$, $V_{DS} = 48\ \text{V}$, $di/dt = 100\ \text{A}/\mu\text{s}$, See Figure 1		90		ns
Q_{RR} Total diode charge			0.2		μC



resistive-load switching characteristics, $T_C = 25^\circ\text{C}$

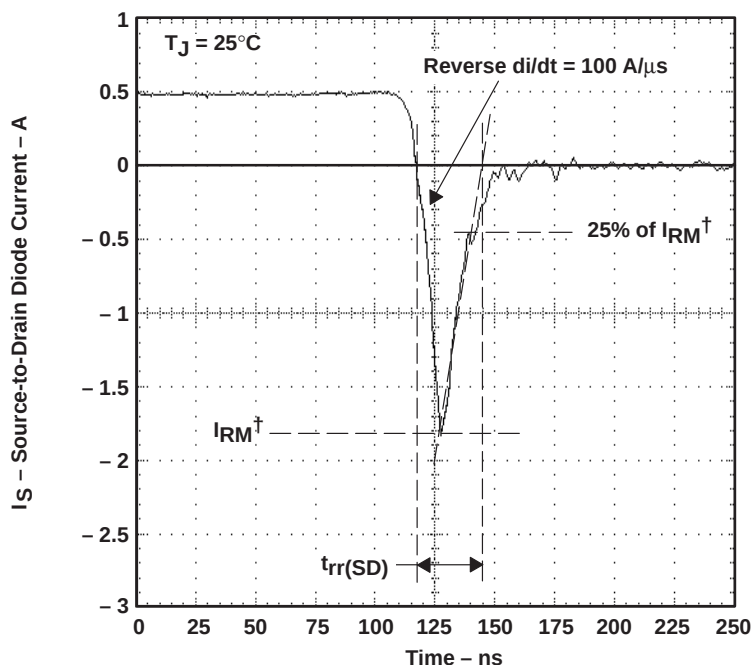
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(\text{on})}$ Turn-on delay time	$V_{DD} = 25\text{ V}$, $R_L = 50\ \Omega$, $t_{\text{en}} = 10\text{ ns}$, $t_{\text{dis}} = 10\text{ ns}$, See Figure 2		21	42	ns
$t_{d(\text{off})}$ Turn-off delay time			20	40	
t_r Rise time			5	10	
t_f Fall time			13	26	
Q_g Total gate charge	$V_{DS} = 48\text{ V}$, $I_D = 0.5\text{ A}$, $V_{GS} = 10\text{ V}$, See Figure 3		3.1	3.8	nC
$Q_{gs(\text{th})}$ Threshold gate-to-source charge			0.4	0.5	
Q_{gd} Gate-to-drain charge			1.3	1.6	
L_D Internal drain inductance			5		nH
L_S Internal source inductance			5		
R_g Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction-to-ambient thermal resistance	All outputs with equal power, See Note 4		130		$^\circ\text{C/W}$
$R_{\theta JP}$ Junction-to-pin thermal resistance			44		

NOTE 4: Package mounted on an FR4 printed-circuit board with no heat sink

PARAMETER MEASUREMENT INFORMATION



$^\dagger I_{RM}$ = maximum recovery current

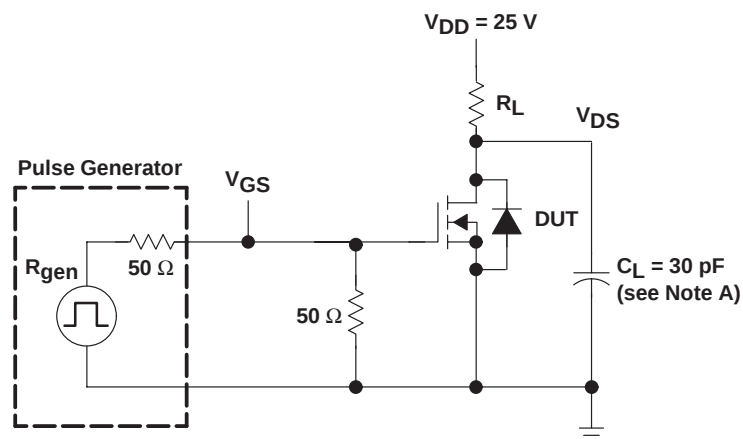
Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode

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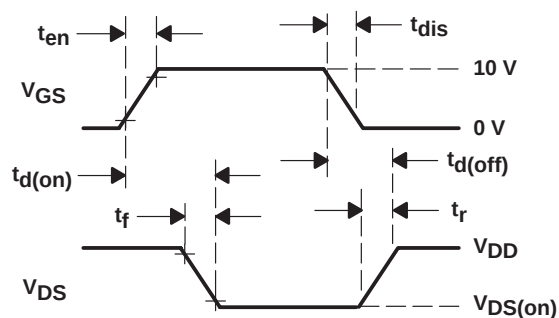
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PARAMETER MEASUREMENT INFORMATION



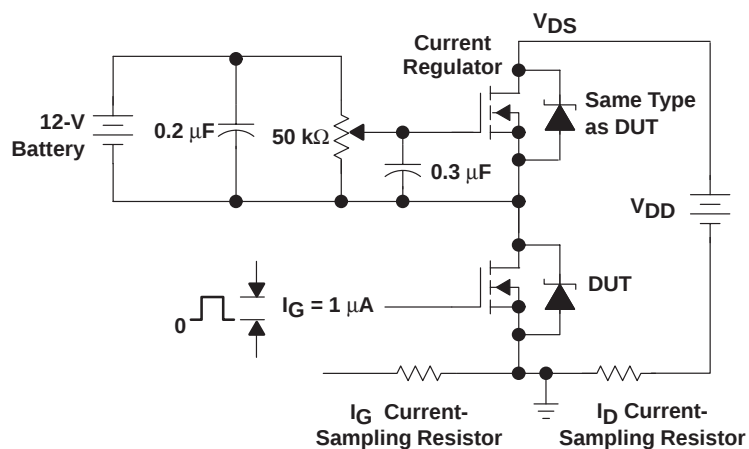
TEST CIRCUIT

NOTE A: C_L includes probe and jig capacitance.

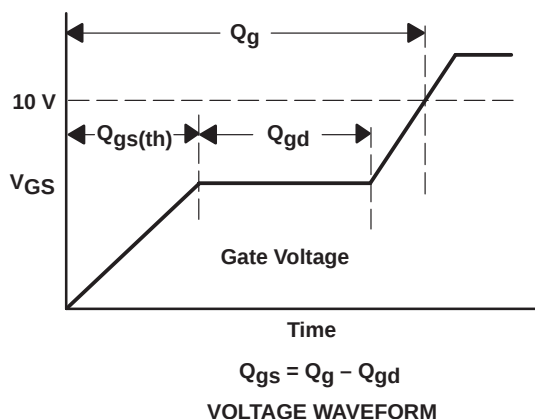


VOLTAGE WAVEFORMS

Figure 2. Resistive-Switching Test Circuit and Voltage Waveforms



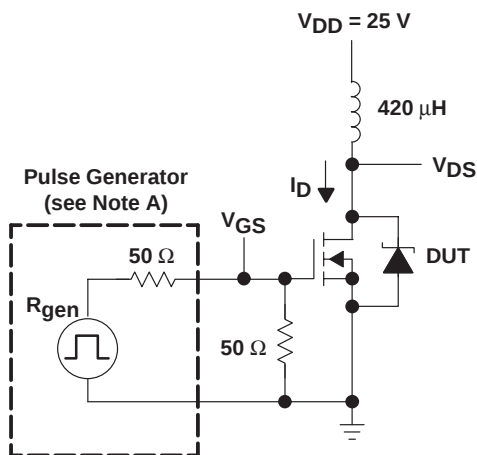
TEST CIRCUIT



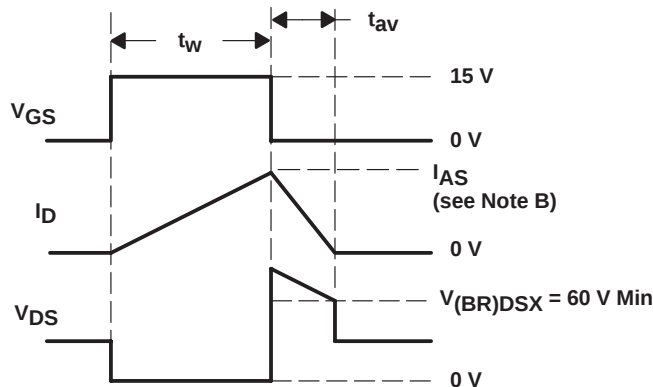
VOLTAGE WAVEFORM

Figure 3. Gate-Charge Test Circuit and Voltage Waveform

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

- NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_0 = 50 \Omega$.
B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 5$ A.

$$\text{Energy test level is defined as } E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 9 \text{ mJ.}$$

Figure 4. Single-Pulse Avalanche-Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

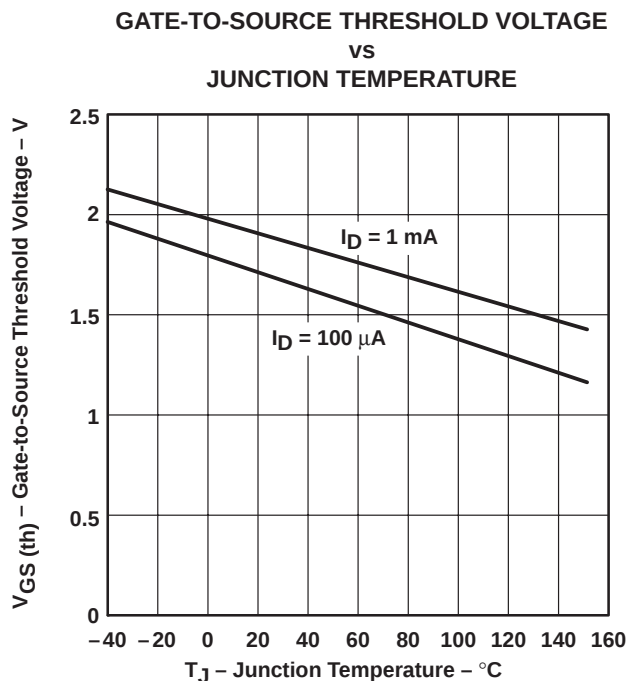


Figure 5

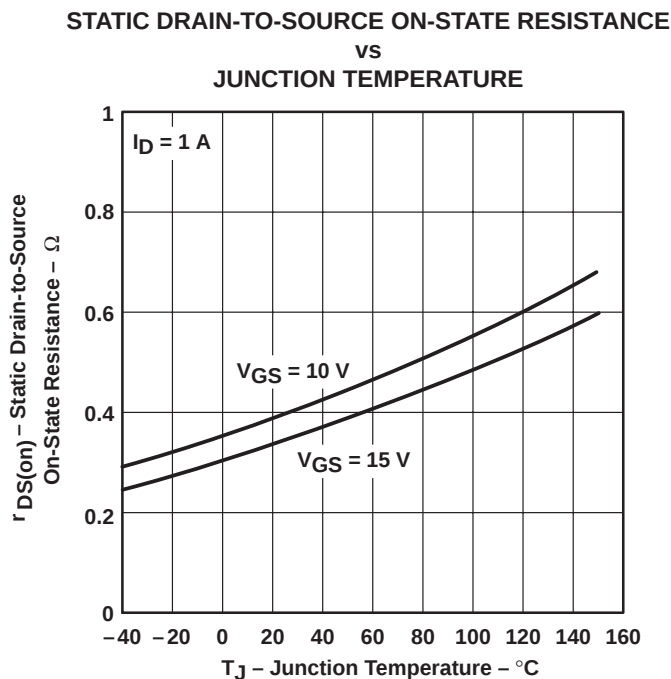


Figure 6

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TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT

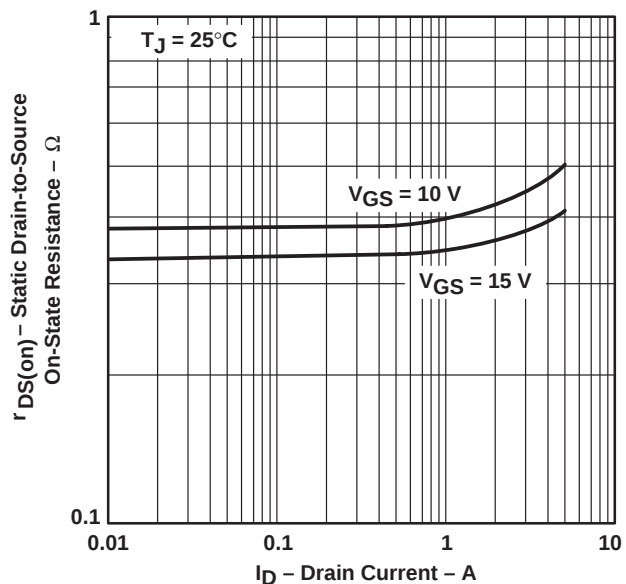


Figure 7

DRAIN CURRENT
vs
DRAIN-TO-SOURCE VOLTAGE

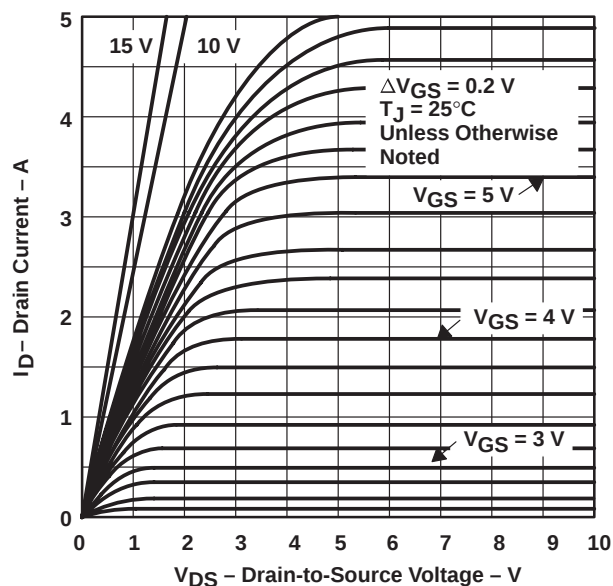


Figure 8

DISTRIBUTION OF
FORWARD TRANSCONDUCTANCE

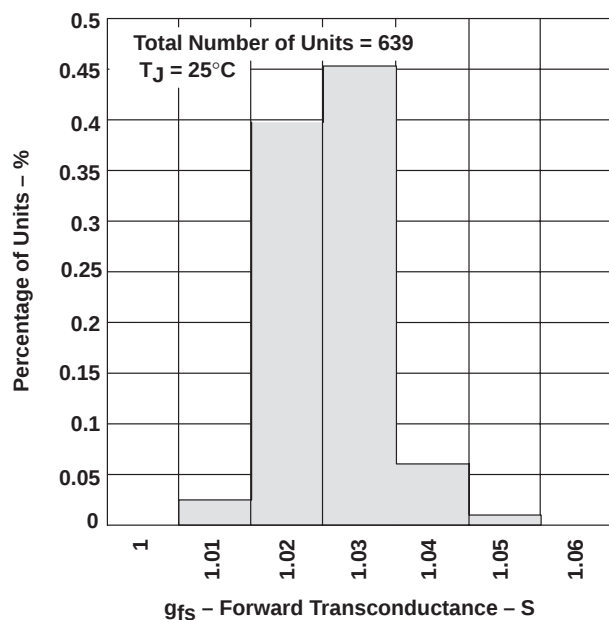


Figure 9

DRAIN CURRENT
vs
GATE-TO-SOURCE VOLTAGE

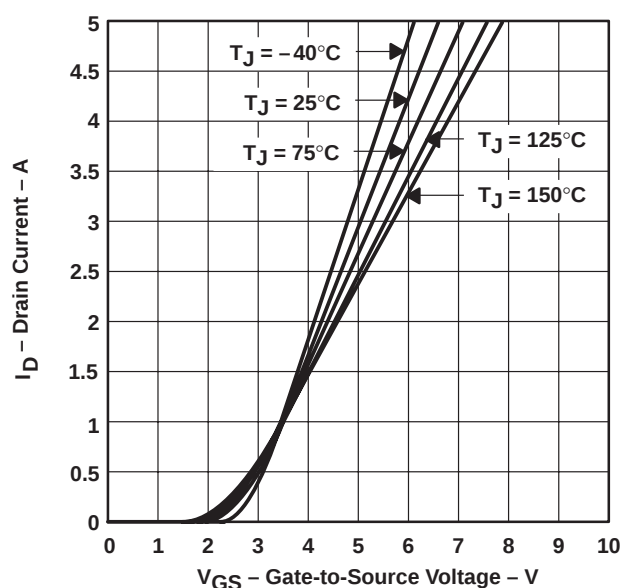


Figure 10

TYPICAL CHARACTERISTICS

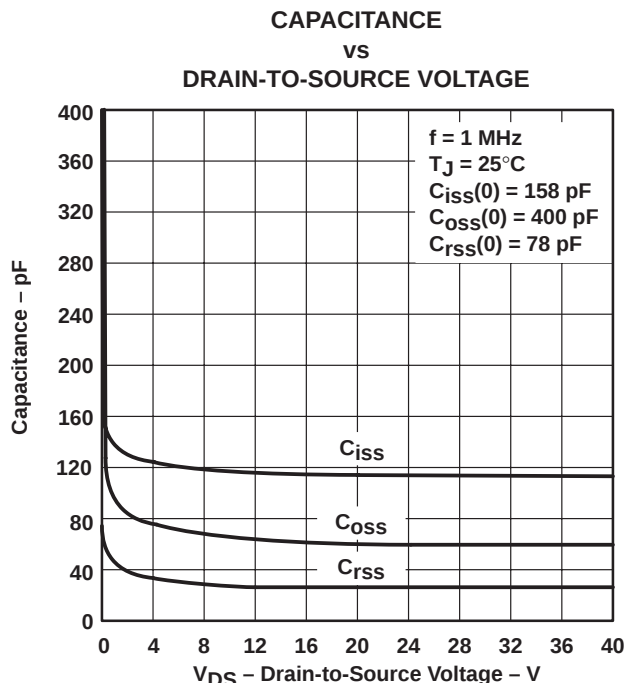


Figure 11

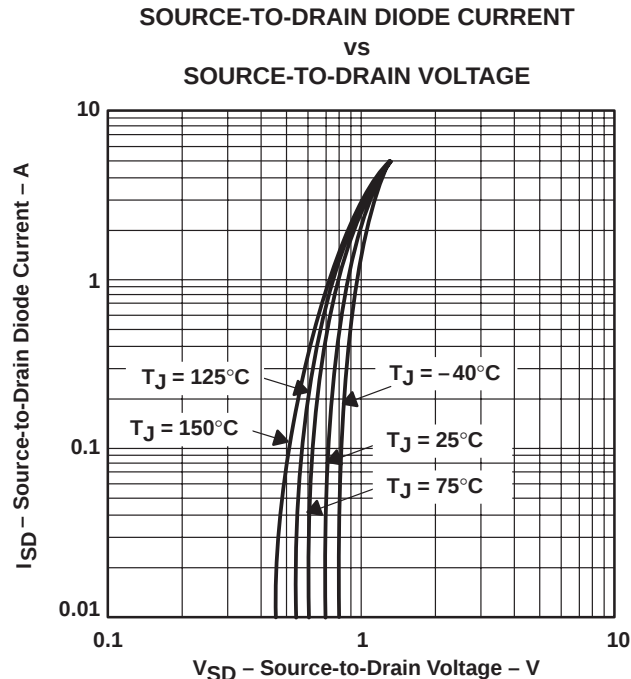


Figure 12

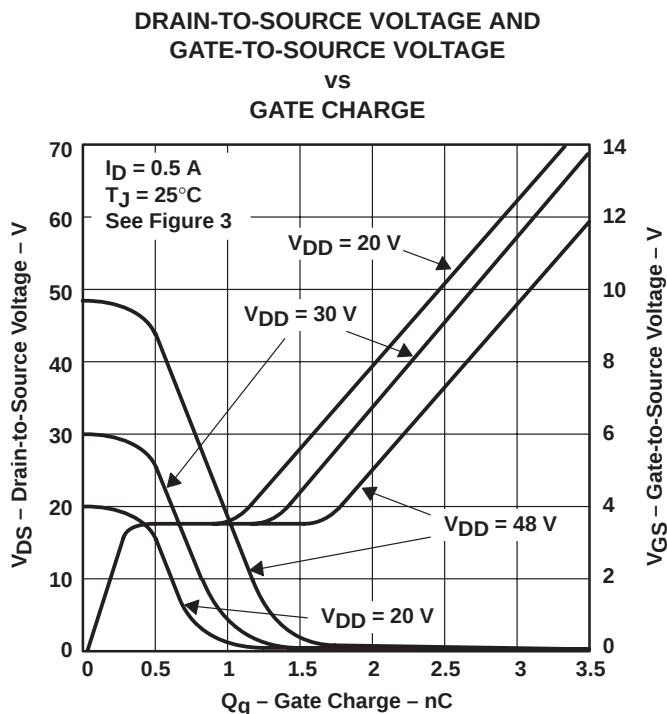


Figure 13

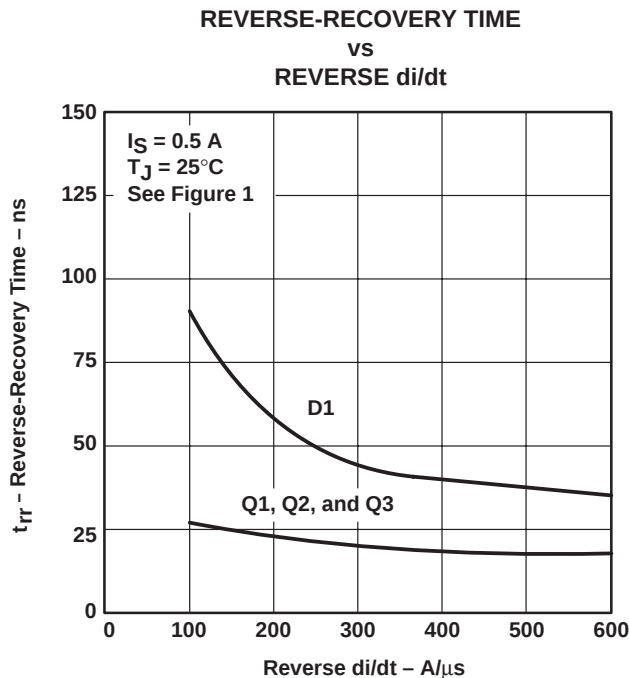


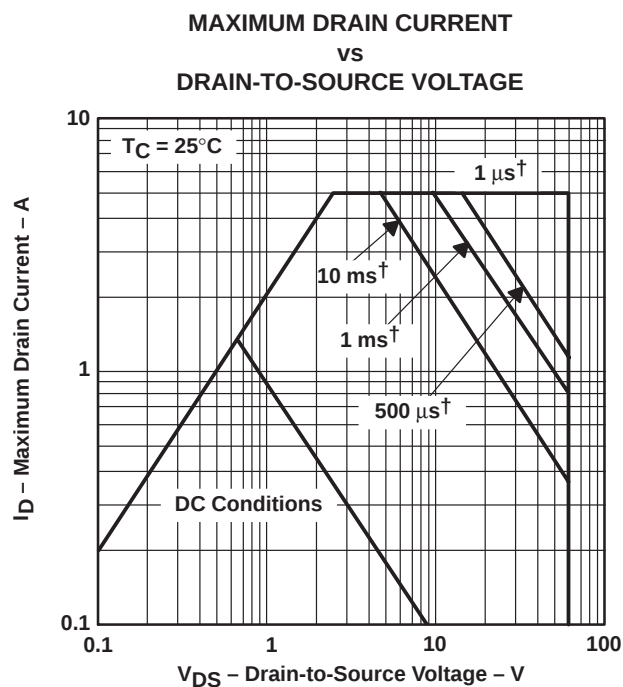
Figure 14

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THERMAL INFORMATION



[†] Less than 0.1 duty cycle

Figure 15

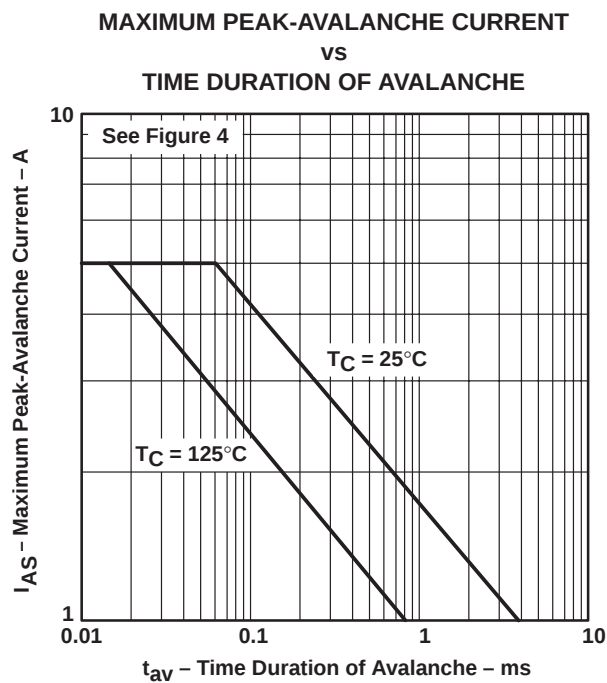
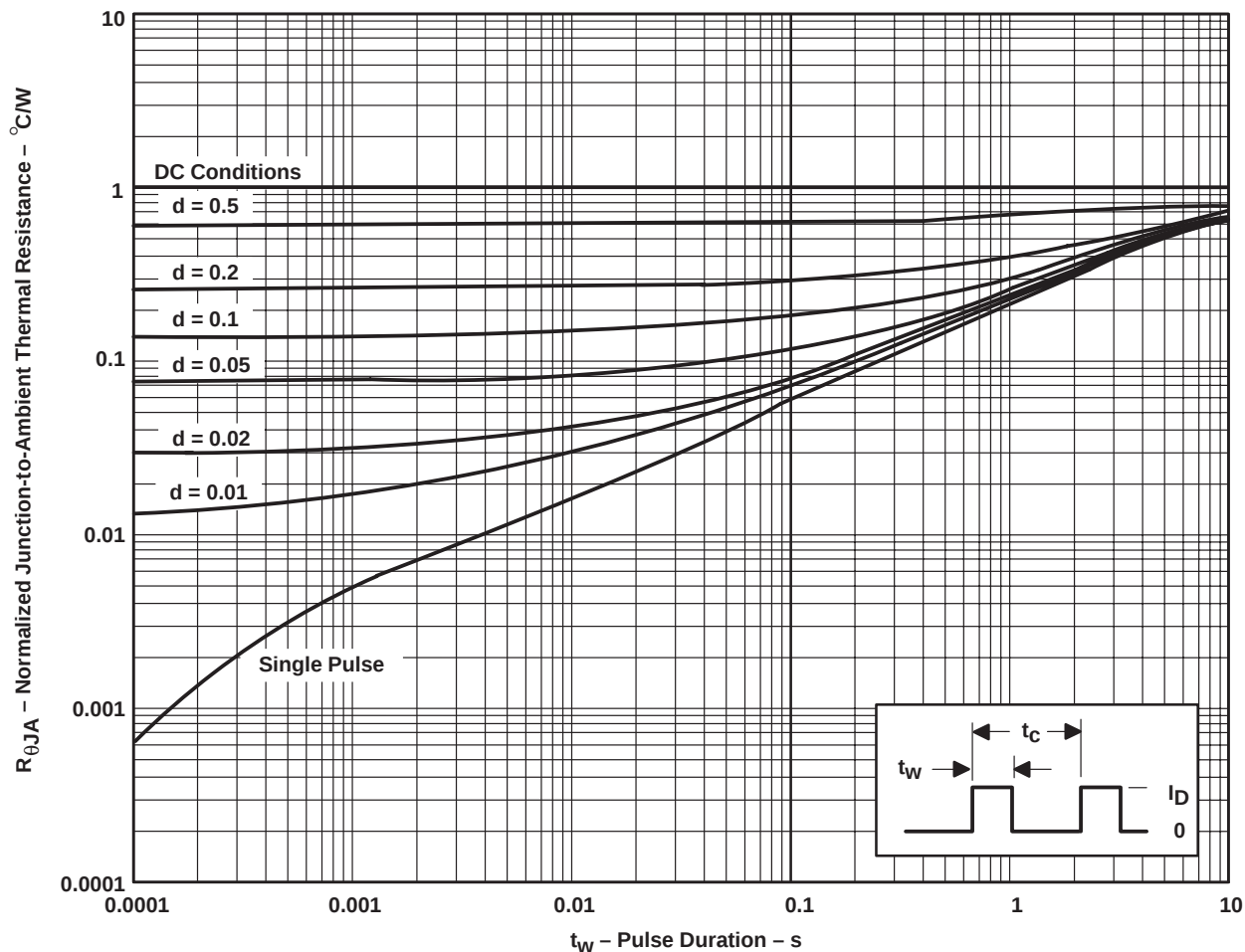


Figure 16

THERMAL INFORMATION

D PACKAGE†
NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE
VS
PULSE DURATION



† Device mounted on FR4 printed-circuit board with no heat sink

NOTES: $Z_{\theta A}(t) = r(t) R_{\theta JA}$
 t_W = pulse duration
 t_C = cycle time
 d = duty cycle = t_W/t_C

Figure 17

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